

Mu2e Calorimeter electronics

E. Pedreschi

INFN Pisa

MUSE Network General Meeting
October 22th 2018

Outline

- Mu2e Calorimeter Electronics
- Front End Electronics - FEE
- DIgitizer ReAdout Controller - DIRAC
- Proto-Slice Test
- DIRAC radiation test.

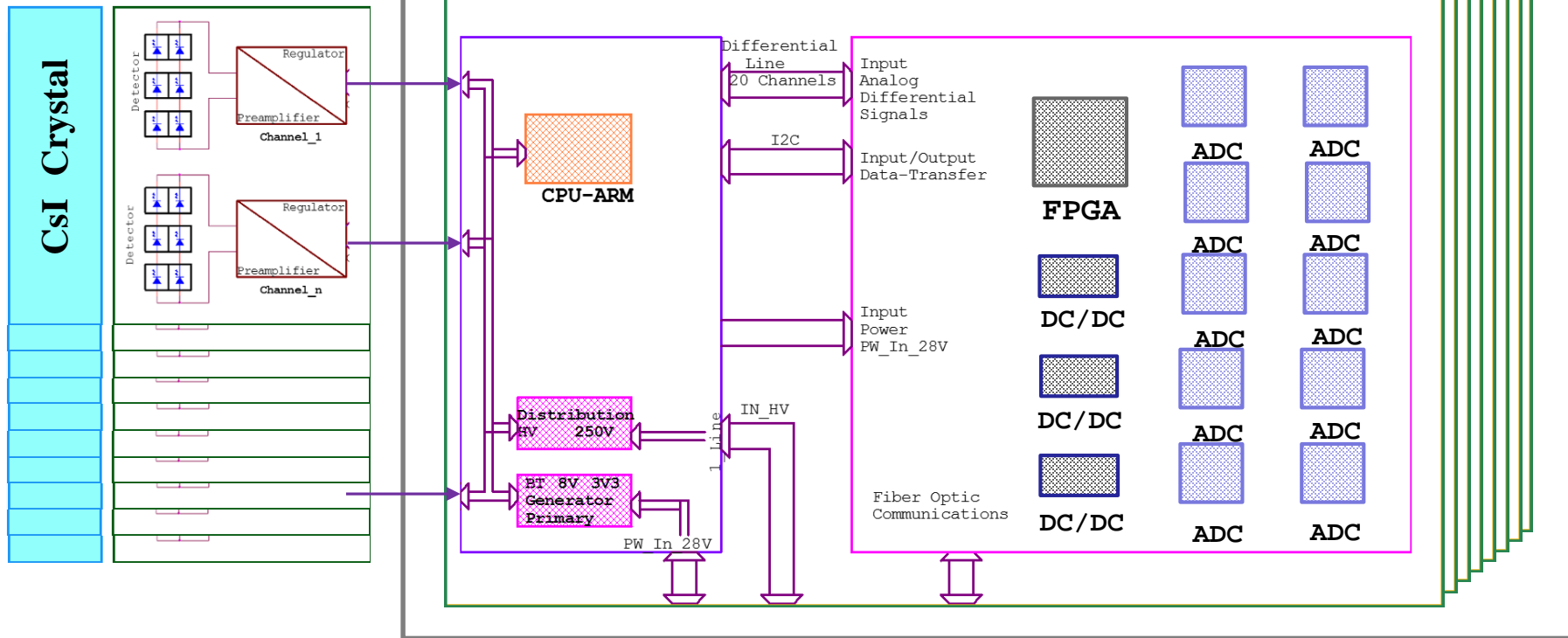
Mu2e Calorimeter Electronics

Disks x 2

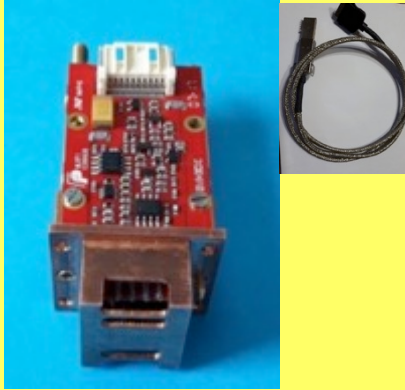
Crate x 10

DIRAC x 8

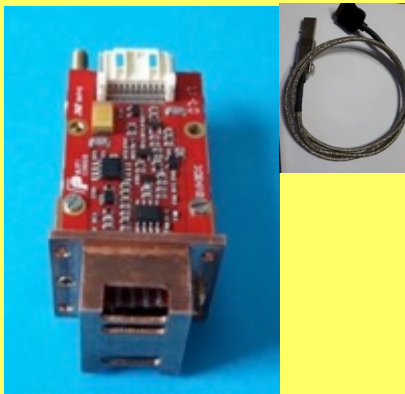
**FEE x10 / board
(SiPM x2 / FEE)**



Mu2e Calorimeter Electronics



X20



X8



X20 (10 + 10)

Some numbers

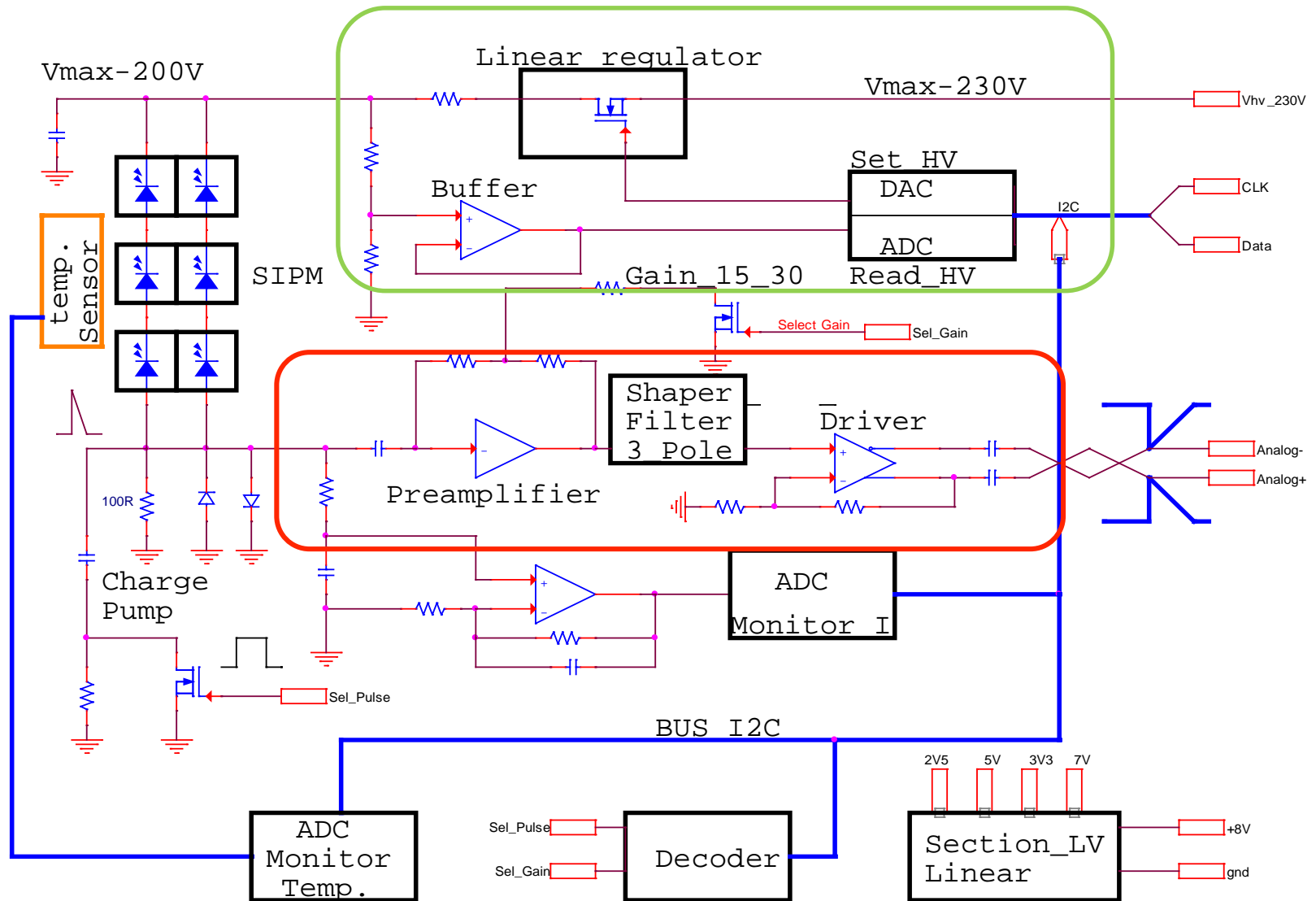
- 2 disks
- 680 crystals/disk
- 2 SiPM/crystal
- $2 \times 2 \times 680 = 2720$ electronic channels
- 20 channels/ digitizer board (DIRAC)
- $2720/20 = 136$
- Each crate hosts 8 DIRAC.

We have to produce:

- 2720 FEE chip cards
- 2720 custom cables
- 136 digitizers & readout boards (DIRAC) + mezzanines
- 20 crates

Front End Electronics - FEE

FEE block diagram



EQUIVALENT CIRCUIT

Regulator specification

➤ Vin max DC	200V
➤ Current limit	2mA
➤ Dynamic regulation	5V ÷ 200V
➤ Setting time	100us
➤ Ramp-up programmable	1ms ÷ 100ms
➤ Ripple (measured)	3 mV (V _{pp})
➤ Power dissipation (min, no load)	50 mW
➤ Power dissipation (Max, with load)	350 mW
➤ Operating temperature	- 40°C ÷ +50 °C
➤ Monitor current detector	50uA ÷ 2mA
➤ Remote control via Dirac interface	I2C
➤ GND insulated from earth	Ceq max 3pf

Amplifier specification

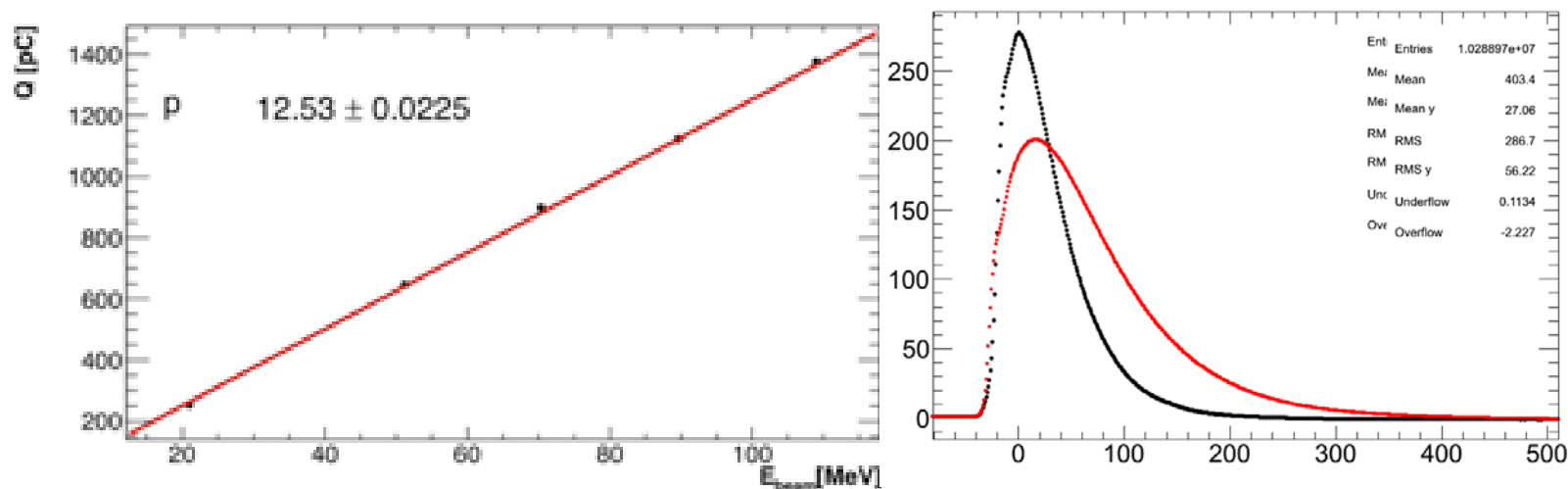
➤ Gain V_{out}/V_{in} 2 steps remote control	$15V \div 30V$
➤ Dynamic differential output	$\pm 1V$
➤ Preamplifier bandwidth	40Mhz
➤ Preamplifier Rise tim	10ns
➤ Output impedance	100 Ω
➤ Coupling output end source	AC
➤ Noise, with source capacity 1pf	$1nV\sqrt{Hz}$
➤ Power dissipation	45mW
➤ Power supply	+8V
➤ Semi-gaussian shaping filter	3 pole
➤ Rise Time after shaper	25ns
➤ Injection test pulse charging, fixed amplitude	400mV
➤ Input protection	10mJ

FEE (AMP-HV)

- AMP-HV is a custom 2-sides board
- Amplifier on A side, Local HV regulator on B-side
- It has a temperature sensor
- It provides I_{dark} measurement, two gains' setting

➔ Differential signals are sent to Mezzanine Board (MB)
and then to the DIRAC board

2 versions up to now ... V1 had some linearity problems solved in V2
Modified shaping time in V2 to increase the leading edge time.
V3 is foreseen to strengthen radiation hardness of the board



Dlgitizer ReAdout Controller DIRAC

DIRAC requirements and specifications

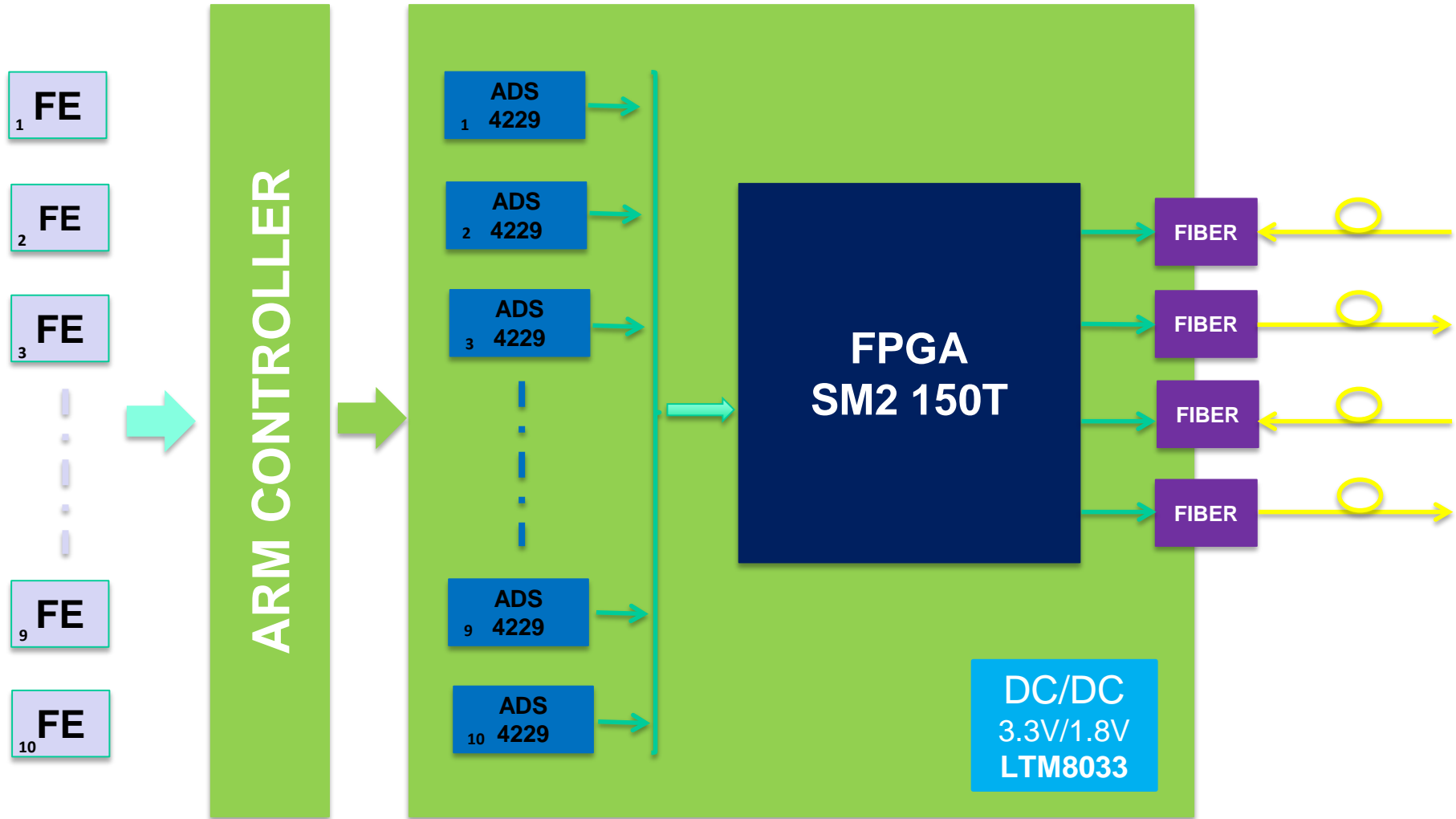
Requirements:

- Sample the SiPM signal (after FEE) to achieve a good energy resolution $O(7-10\%)$ and an optimal time resolution $O(200\text{ ps})$
- Each crystal is readout through 2 SiPM \rightarrow we need to digitize ~ 2700 channels
- Limit the number of pass through connectors

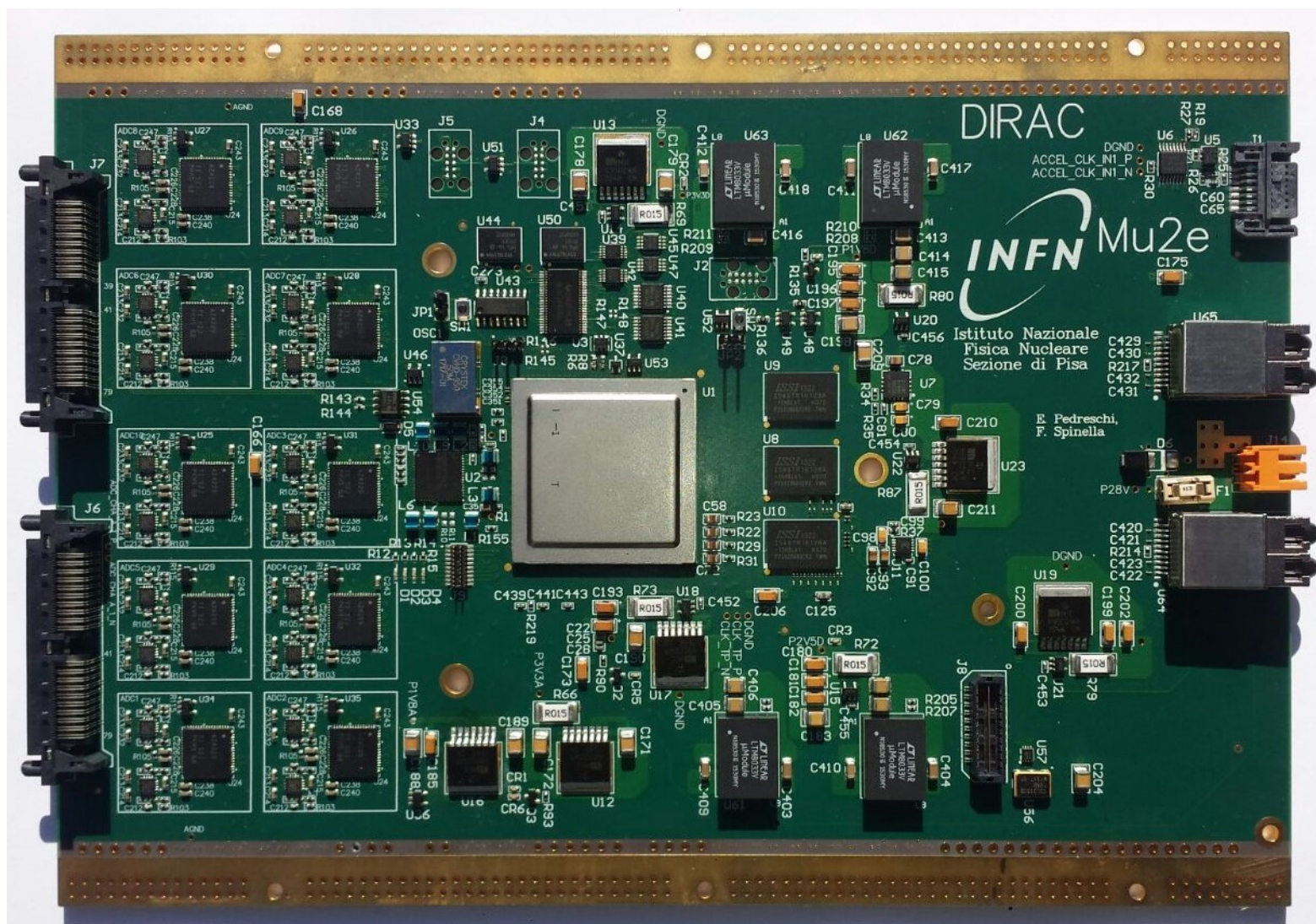
This translates to the following specifications:

1. Sample the signal with an ADC (200 Msamples @ 12 bits)
2. DIRAC is located inside the cryostat:
 - ✓ Stand a radiation environment of 0.2 krad/y of TID (Total Ionizing Dose).
 - ✓ Work in presence of high magnetic field (1T)
 - ✓ Low power
3. Host at least 20 channels/board (mechanical constrains & BW limit)
4. Have large reliability to allow to operate for 1 year w.o. interruption

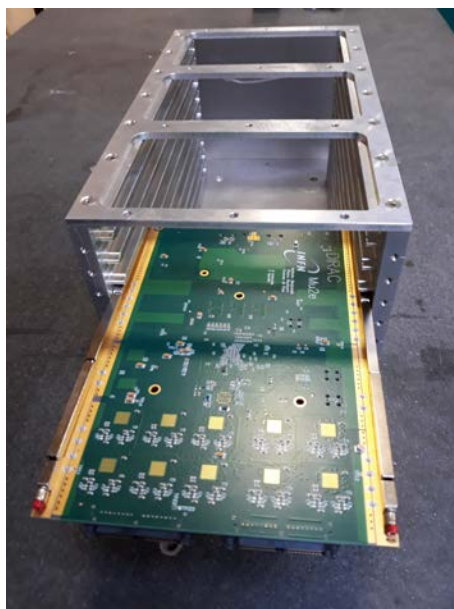
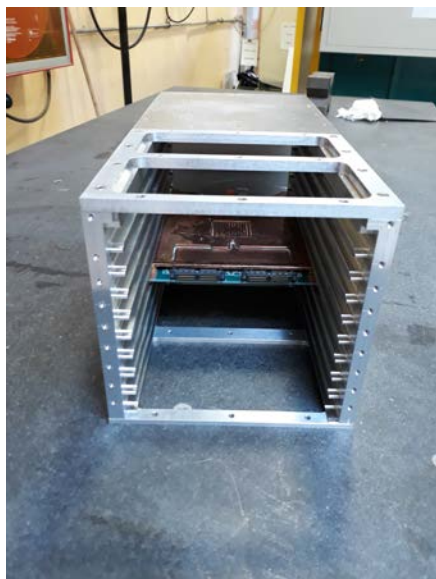
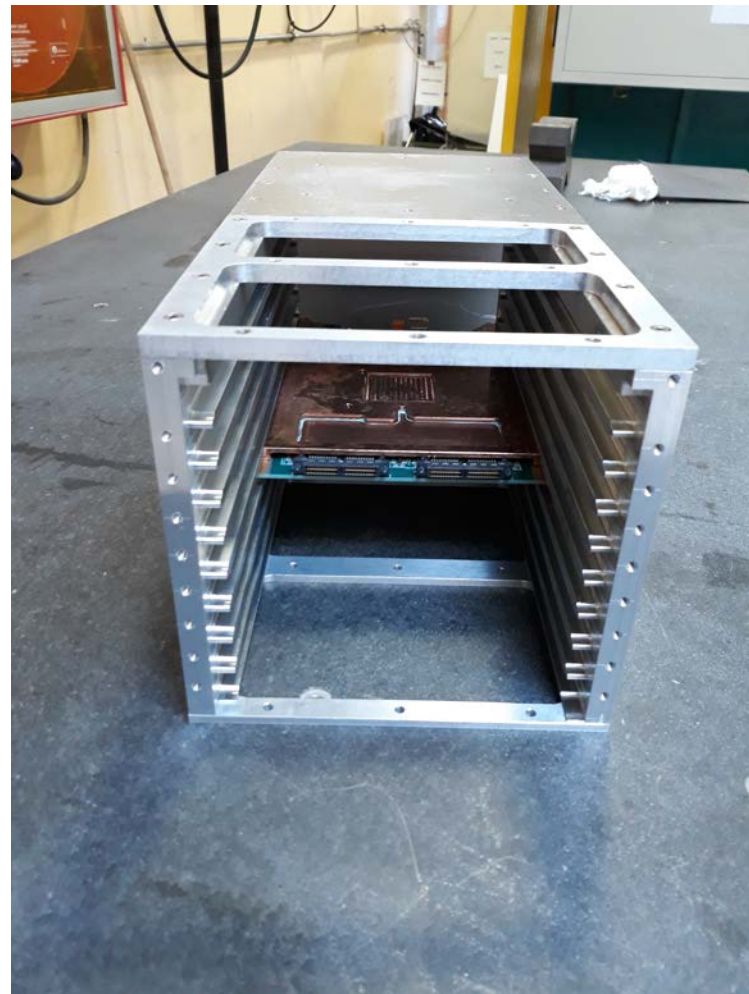
DIRAC Block Diagram



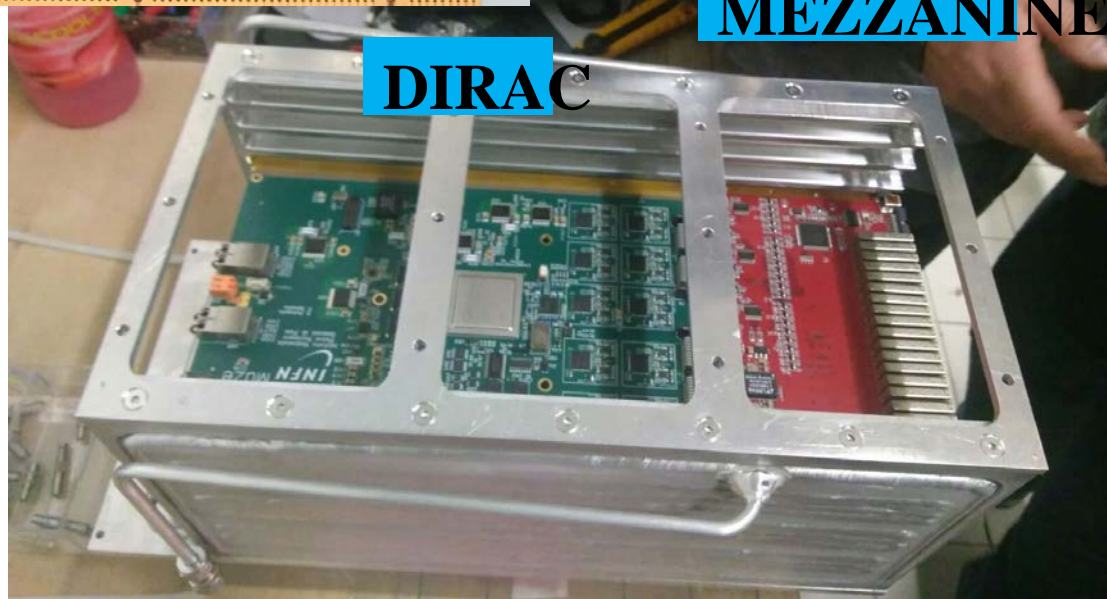
DIRAC V1



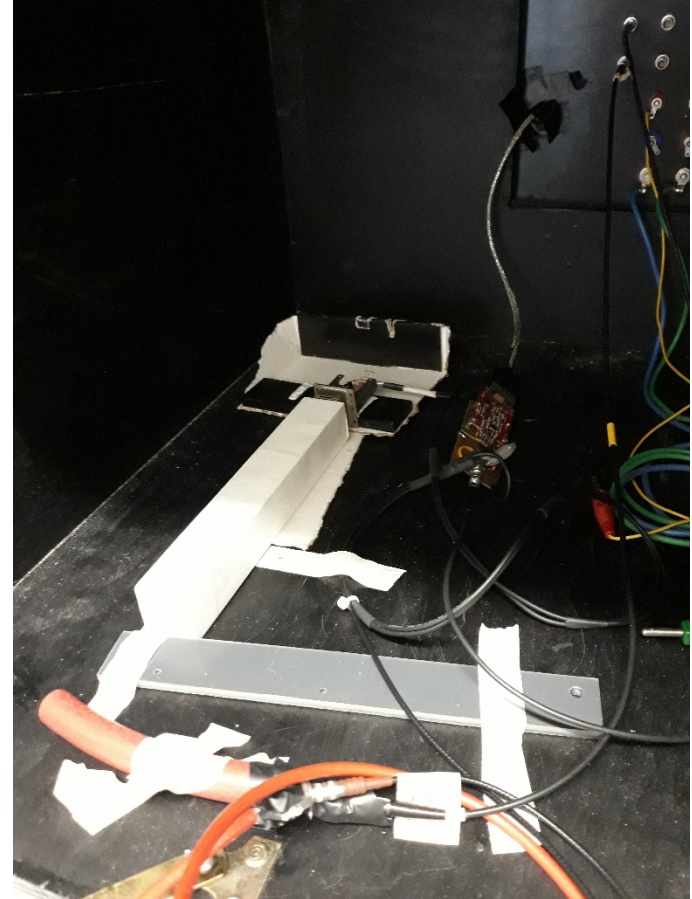
DIRAC V1 + Crate



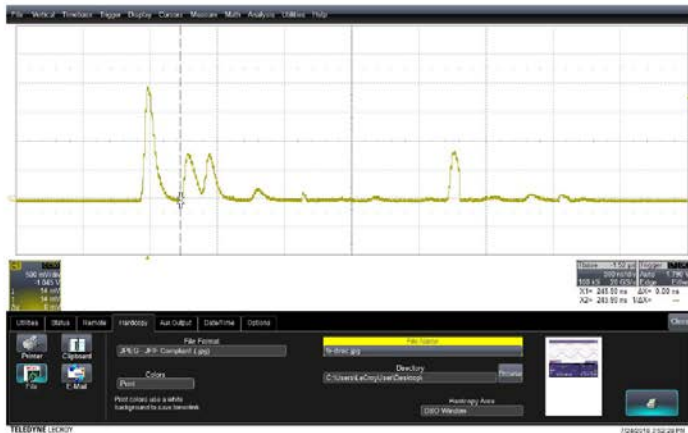
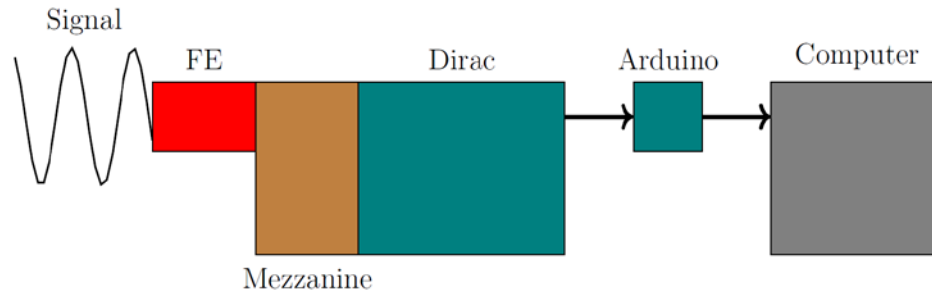
DIRAC V1 + Mezzanine + Crate



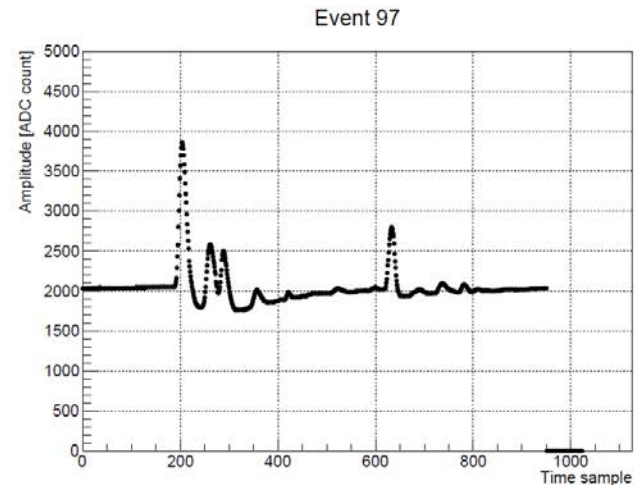
Proto Slice test: full chain, 1 channel



Proto Slice test: injected signal on FEE

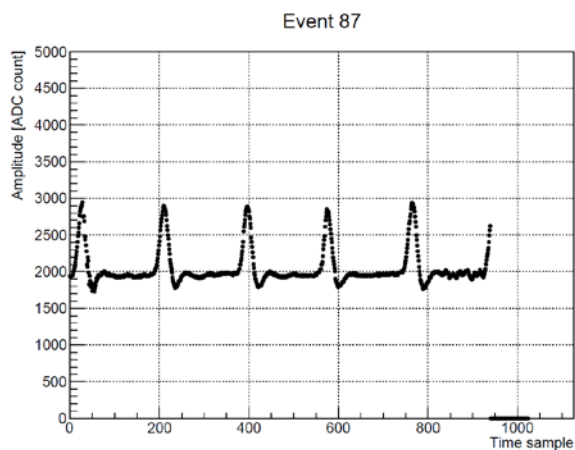
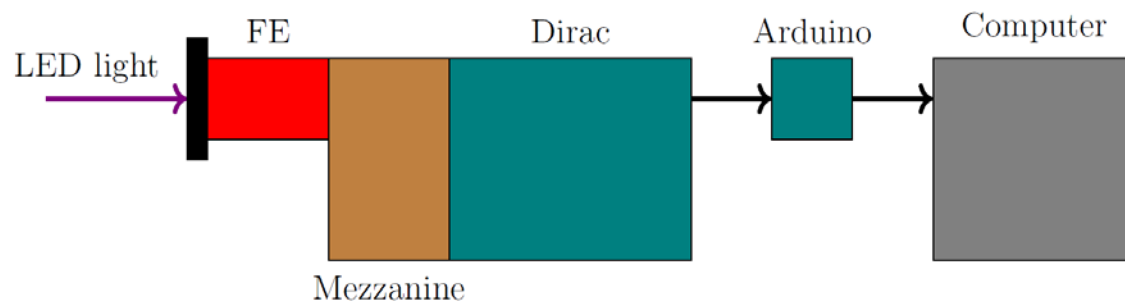


**Electrical signal from
Arbitrary Function Generator**



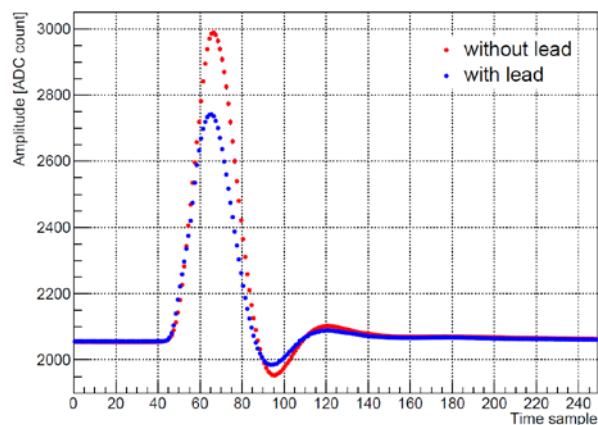
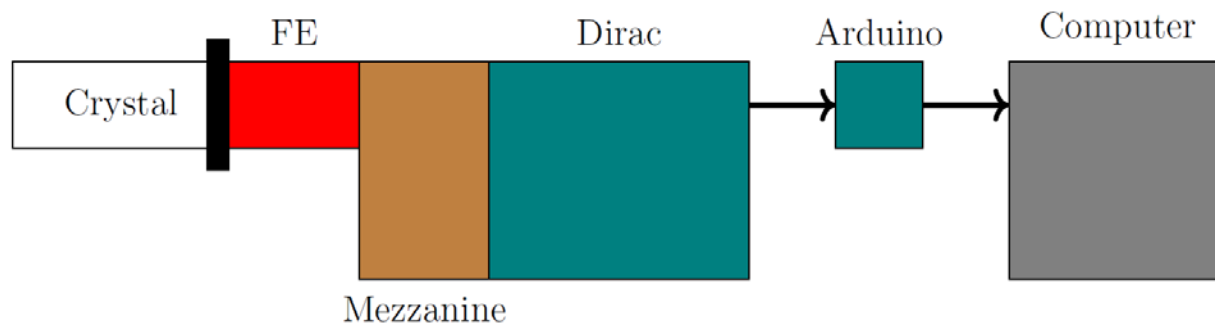
**Readout signal
200 MHz 12 bit**

Proto Slice test: LED + SiPM



Readout signal
200 MHz 12 bit

Proto-Slice test: CsI + SiPM + Cosmic



Readout signal
200 MHz 12 bit

DIRAC V1 status

- Full chain test for 1 channel
- 20 channels firmware already in place. Currently we are optimizing clock constraints to reach 200 MHz on all channels
- NO design issues up to now

Towards V2 ...

- A version V2 is currently under design.
- We will replace some components (FPGA, fiber optics transceiver, DCDC converter) to increase radiation strength
- Most of components (e.g. ADCs) will not be changed in V2 release.

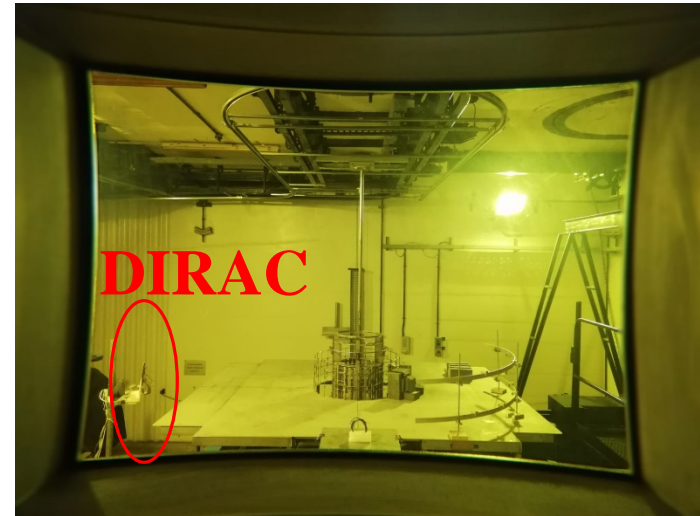
DIRAC radiation test

- DIRAC board must be qualified to be used in a radiation environment
- Several tests are required:
 1. Total Ionizing Dose (TID)
 2. Displacement Damage (DD) Neutrons
 3. Single Event Effects (SEEs)

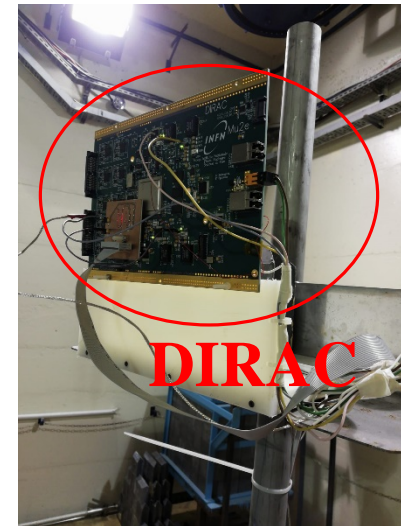
TID tests on V1 done few months ago, DD done only on few components, SEEs foreseen next year on V2

Expected TID ≈ 0.2 Krad/y \rightarrow 1 Krad in 5 years. Collaboration requires an acceptance test with a safety factor 12 \rightarrow we have to qualify DIRAC for TID up to 12 Krad dose

TID test @ ENEA Casaccia (1)

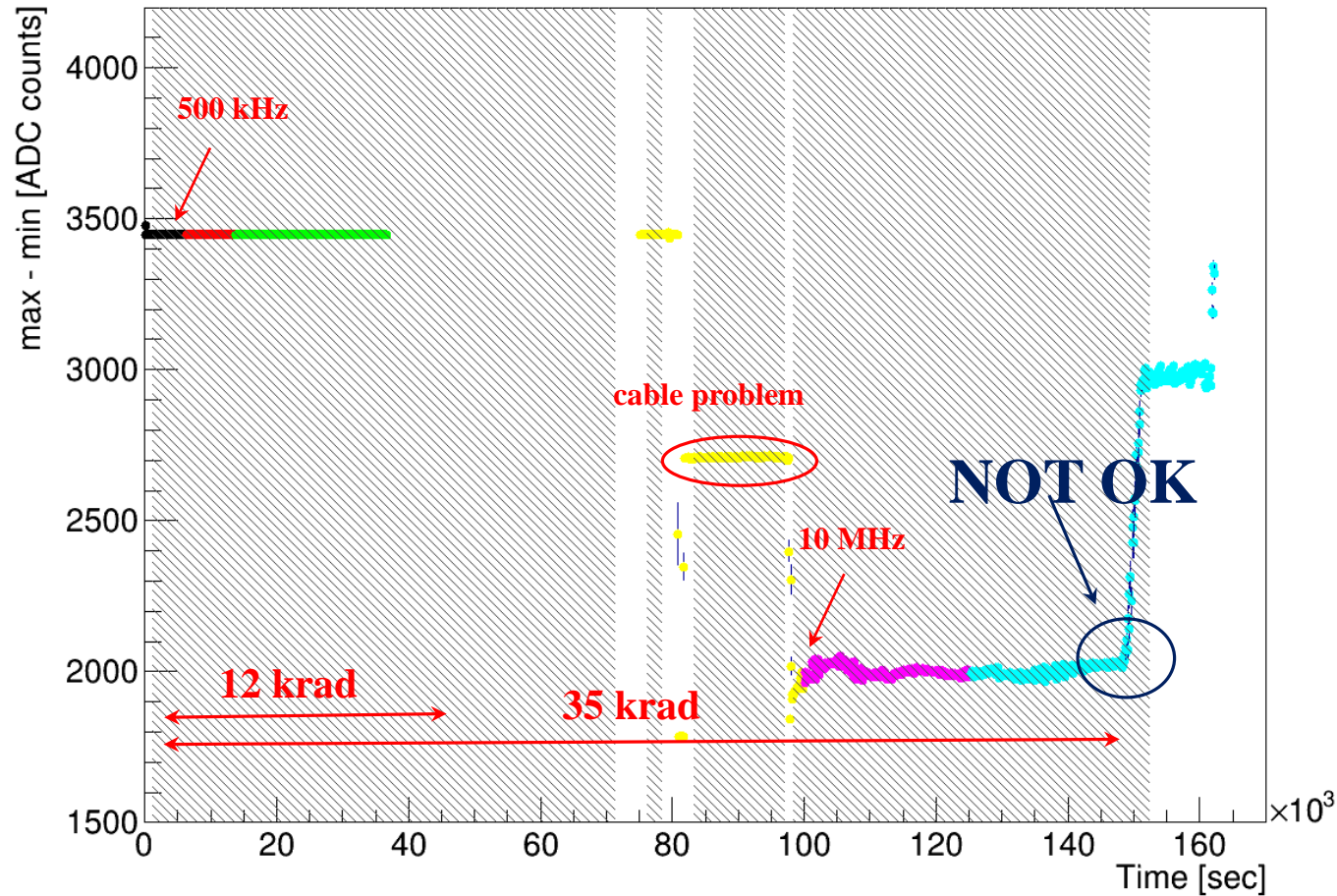


- Co60 source
- Full board test
- Dose is function of distance -> max 2 krad/h
 - ✓ Tested at 1 Krad/h
- Start: June 13 @ 1.30 PM
- Stop: June 15 @ 9.20 AM
- Dose requested: 1Krad/ h
- Total dose: ≈ 41 krad

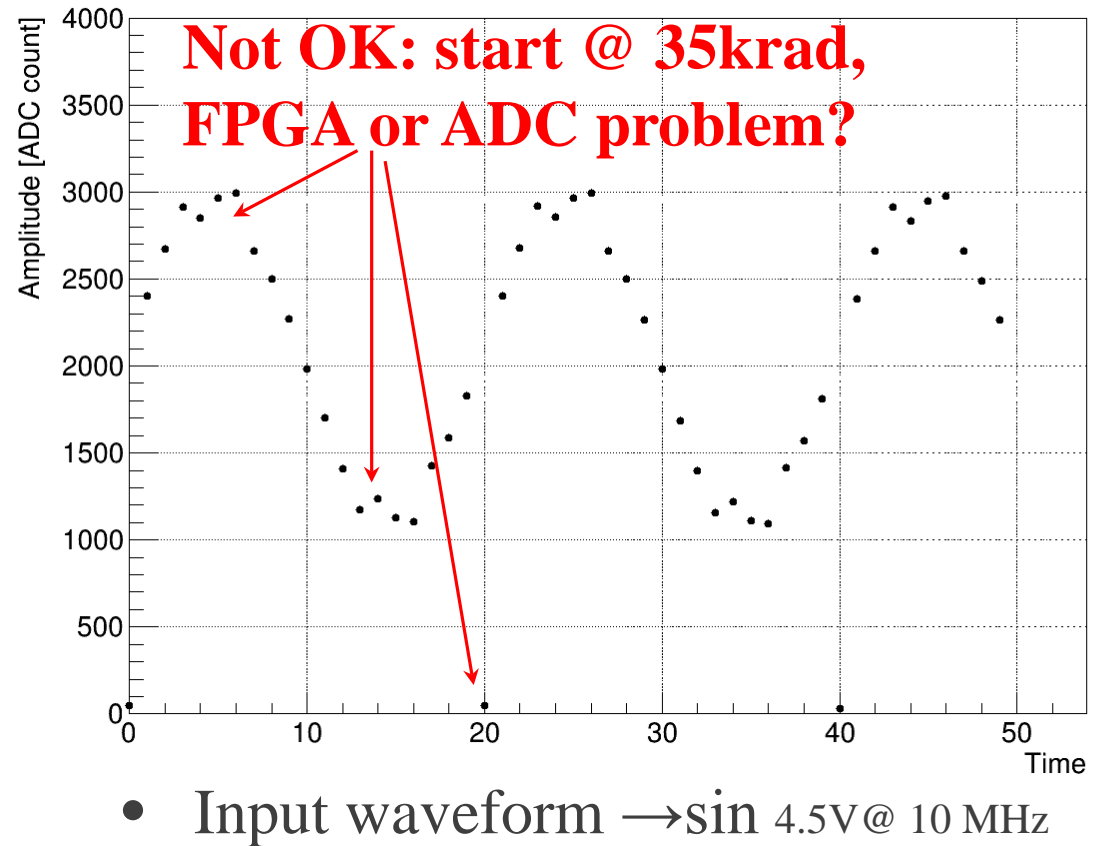
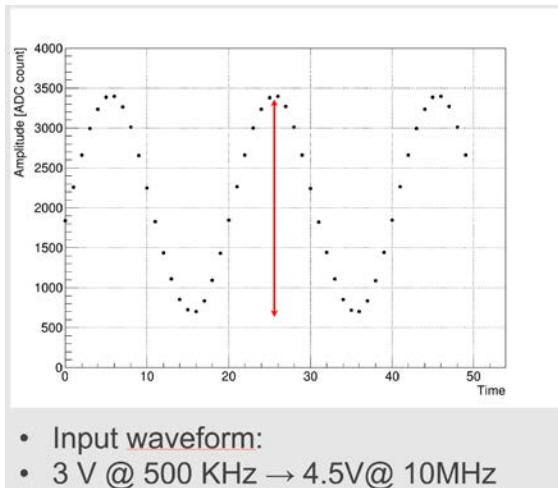
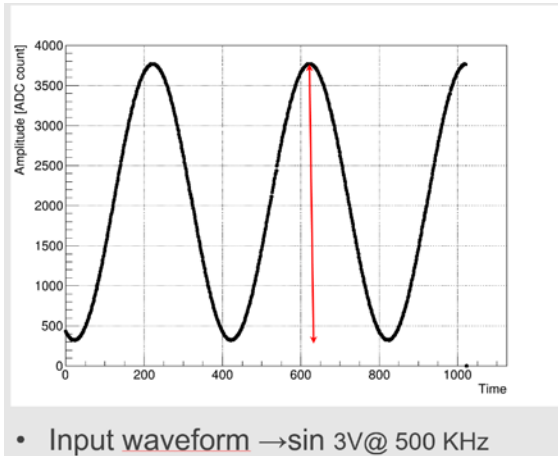


TID test @ ENEA Casaccia (2)

Peak-peak



TID test @ ENEA Casaccia (3)



TID test @ ENEA Casaccia: results

- 41 h beam time
- Nominal Dose Rate (NDR) $\approx 1\text{krad/h}$
- Total dose $\approx 41\text{krad}$
- No evidence of broken components up to 30 krad
 - ✓ Could be ADC or FPGA
- After 41 krad SM2 ARM does not restart after power cycle
- DCDC converters voltage increase: $\approx 20\%$ @ 41 krad

Thank you!